

PATENT ABSTRACTS OF JAPAN

(11)Publication number : **2001-168387**
(43)Date of publication of application : **22.06.2001**

(51)Int.CI.

HO1L 33/00
HO1L 31/02
// HO1L 21/205

(21)Application number : **2000-191779**
(22)Date of filing : **26.06.2000**

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(30)Priority

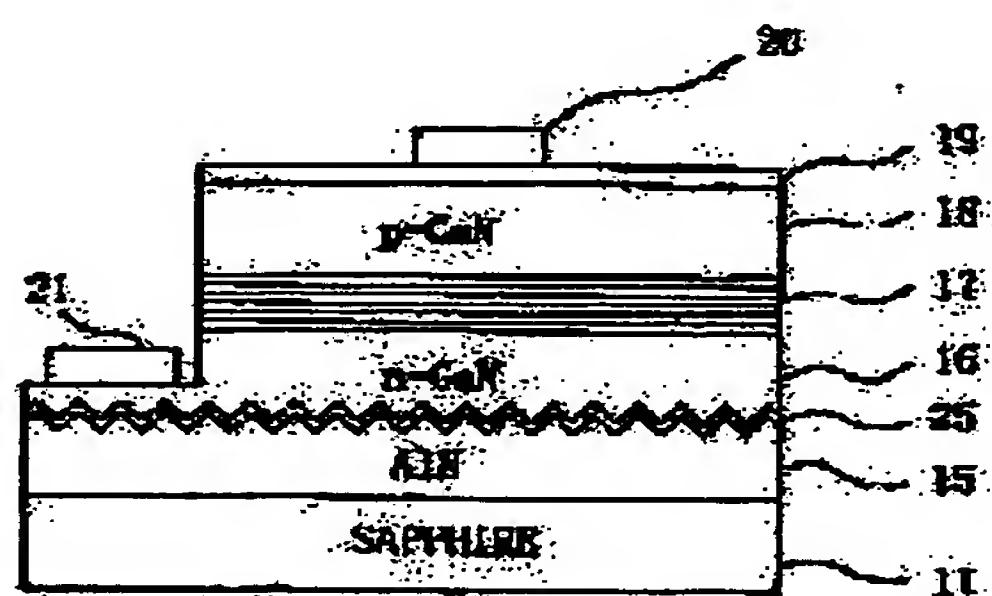
Priority number : **11276556** Priority date : **29.09.1999** Priority country : **JP**

(54) III NITRIDE COMPOUND SEMICONDUCTOR ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To substantially totally reflect a light from a III-nitride compound semiconductor in a substrate layer having a textured structure, a sectional trapezoidal shape or a pit-like surface shape.

SOLUTION: A reflecting layer made of a nitride of one or more types of metals selected from titanium, zirconium, hafnium and tantalum is formed on the textured structure, sectional trapezoidal shape or the pit-like surface of the substrate layer. The surface structure of the substrate layer is reflected, and the surface of the reflecting layer is also the textured structure, the sectional trapezoidal shape or the pit-like state.



LEGAL STATUS

[Date of request for examination] **30.09.2003**

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application]

converted registration]
[Date of final disposal for application]
[Patent number] 3633447
[Date of registration] 07.01.2005
[Number of appeal against examiner's decision of
rejection]
[Date of requesting appeal against examiner's
decision of rejection]
[Date of extinction of right]

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